

# Single Phase Fast Recovery Bridge (Power Modules), 61 A



PRIMARY CHARACTERISTICS					
V <sub>RRM</sub>	600 V				
I <sub>0</sub>	61 A				
t <sub>rr</sub>	170 ns				
Туре	Modules - Bridge, Fast				
Package	SOT-227				
Circuit configuration	Single phase bridge				

#### **FEATURES**







- · Simplified mechanical designs, rapid assembly
- Excellent power/volume ratio
- · Designed and qualified for industrial and consumer level
- UL approved file E78996



· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **DESCRIPTION**

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
1		61	A			
10	T <sub>C</sub>	57	°C			
I <sub>FSM</sub>	50 Hz	300	Λ			
	60 Hz	310	Α			
l <sup>2</sup> t	50 Hz	442	A2-			
	60 Hz	402	A <sup>2</sup> s			
V <sub>RRM</sub>		600	V			
T <sub>J</sub>		-55 to +150	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> MAXIMUM mA		
SA61BA60	60	600	700	10		



#### www.vishay.com

# Vishay Semiconductors

FORWARD CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum DC output current		Resistive or inductive load		61	Α		
at case temperature	lo				57	°C	
		t = 10 ms	No voltage		300		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		310	A	
non-repetitive forward current	I <sub>FSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		250	] ^	
		t = 8.3 ms	reapplied	Initial T <sub>J</sub> =	260		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied	T <sub>J</sub> maximum	442		
		t = 8.3 ms			402	A <sup>2</sup> s	
		t = 10 ms	100 % V <sub>RRM</sub>		313		
		t = 8.3 ms	reapplied		284	1	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	$I^2t$ for time $t_x = I_2\sqrt{t} \times \sqrt{t_x}$ ; $0.1 \le t_x \le 10$ ms, $V_{RRM} = 0$ V			4.4	kA²√s	
Value of threshold voltage	V <sub>F(TO)</sub>	T <sub>J</sub> maximum			0.914	V	
Forward slope resistance	r <sub>t</sub>				10.5	mΩ	
Maximum forward voltage drep	V	$T_{J} = 25  ^{\circ}\text{C},  I_{FM} = 30  A_{pk}$ $T_{J} = T_{J}  \text{maximum},  I_{FM} = 30  A_{pk}$ $t_{p} = 400  \mu \text{s}$		1.33			
Maximum forward voltage drop	$V_{FM}$			$T_J = T_J$ maximum, $I_{FM} = 30 A_{pk}$	$t_p = 4$		1.23
RMS isolation voltage base plate	V <sub>ISOL</sub>	f = 50 Hz, t = 1 s		3000			

RECOVERY CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Payarea recovery time typical		$T_J = 25  ^{\circ}\text{C}, \ I_F = 20  \text{A}, \ V_R = 30  \text{V}, \ dI_F/dt = 100  \text{A}/\mu\text{s}$	170	ns		
Reverse recovery time, typical	t <sub>rr</sub>	$T_J = 125 ^{\circ}\text{C},  I_F = 20  \text{A},  V_R = 30  \text{V},  \ dI_F/dt = 100  \text{A}/\mu\text{s}$	250	12		
Reverse recovery current, typical	I <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C}, \ I_F = 20  \text{A}, \ V_R = 30  \text{V}, \ dI_F/dt = 100  \text{A}/\mu\text{s}$	10.5	A	I <sub>FM</sub> t <sub>rr</sub>	
		$T_J = 125 ^{\circ}\text{C}, I_F = 20 \text{A}, V_R = 30 \text{V}, \\ dI_F/dt = 100 \text{A/}\mu\text{s}$	16			
D	Q <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C},  I_F = 20  \text{A},  V_R = 30  \text{V},  \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	900	nC	$\frac{dI_{R}}{dt}$ $I_{RM(REC}$	
Reverse recovery charge, typical		$T_J = 125 ^{\circ}\text{C}, I_F = 20 \text{A}, V_R = 30 \text{V}, \\ dI_F/dt = 100 \text{A/}\mu\text{s}$	1970	iiC		
Snap factor, typical	S	T <sub>J</sub> = 25 °C	0.6			
Junction capacitance, typical	C <sub>T</sub>	V <sub>R</sub> = 600 V	67	pF		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55	-	150	°C
Thermal resistance junction to case, per diode	В		-	=.	1.2	
Thermal resistance junction to case, per module	R <sub>thJC</sub>		-	-	0.30	°C/W
Thermal resistance case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting toward		Torque to terminal	-	=.	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	=.	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			

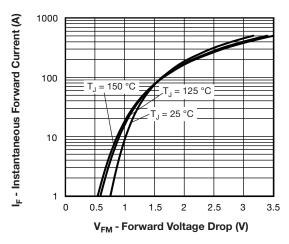


Fig. 1 - Typical Forward Voltage Drop Characteristics

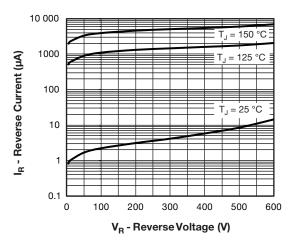


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

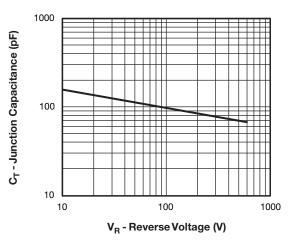


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

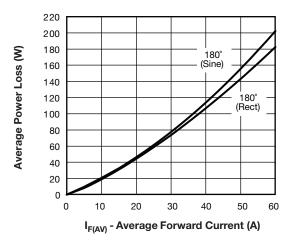


Fig. 4 - Current Rating Characteristics

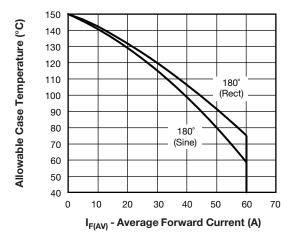


Fig. 5 - Forward Power Loss Characteristics



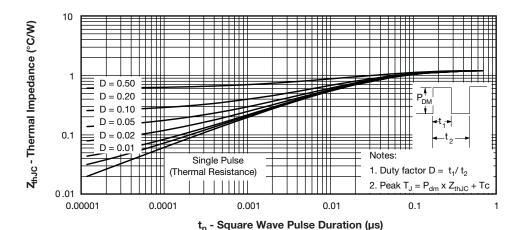


Fig. 6 - Typical Forward Voltage Drop Characteristics

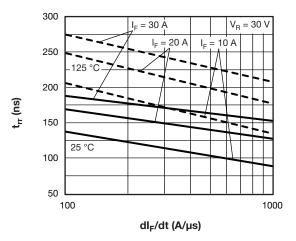


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

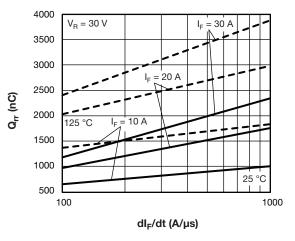


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

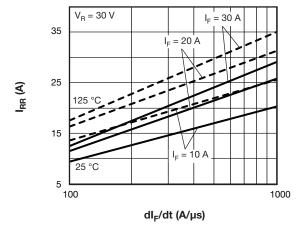


Fig. 9 - Typical Reverse Recovery Current vs.  $dI_F/dt$ 

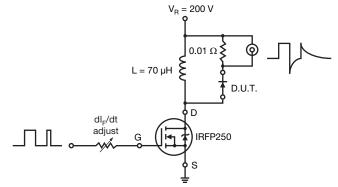
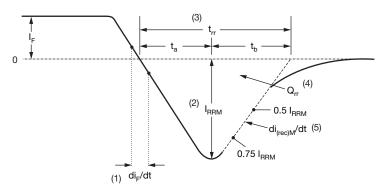


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

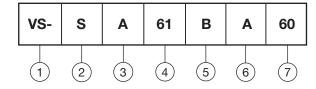
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

#### Device code



- 1 Vishay Semiconductors product
- S = fast recovery diode
- A = present silicon generation
- Current rating (61 = 61 A)
- 5 Circuit configuration:
  - B = single phase bridge
- 6 Package indicator:

A = SOT-227, standard insulated base

7 - Voltage rating (60 = 600 V)



CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Single phase bridge	В	Lead Assignment  (AC) 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4 0 4				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95423			
Packaging information	www.vishay.com/doc?95425			

### SOT-227 Generation 2

#### **DIMENSIONS** in millimeters (inches)





#### Note

· Controlling dimension: millimeter



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